

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

GBP2005-MS THRU GBP210-MS

Product specification

VOLTAGE RANGE: 50 - 1000V
CURRENT: 2 A

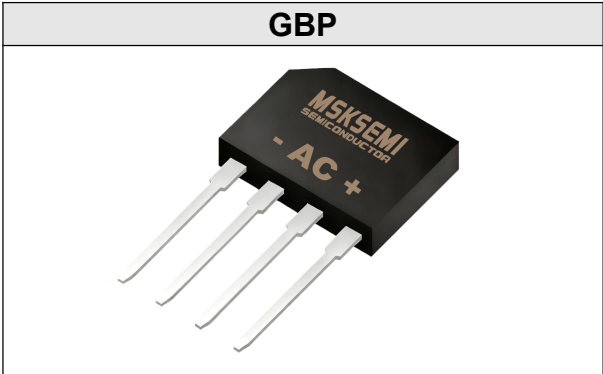
FEATURES

- Glass Passivated Die Construction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- Ideal for Printed Circuit Boards

MECHANICAL DATA

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Weight: 2.0 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

REFERENCE NEWS



Marking

GBP2005-MS	GBP201-MS	GBP202-MS	GBP204-MS
<div>MSKSEMI GBP2005 + AC -</div>	<div>MSKSEMI GBP201 + AC -</div>	<div>MSKSEMI GBP202 + AC -</div>	<div>MSKSEMI GBP204 + AC -</div>
GBP206-MS	GBP208-MS	GBP210-MS	
<div>MSKSEMI GBP206 + AC -</div>	<div>MSKSEMI GBP208 + AC -</div>	<div>MSKSEMI GBP210 + AC -</div>	

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ unless otherwise specified
 Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	GBP 2005-MS	GBP 201-MS	GBP 202-MS	GBP 204-MS	GBP 206-MS	GBP 208-MS	GBP 210-MS	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current @ $T_A = 50^\circ\text{C}$	Io	2.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	50							A
Forward Voltage (per bridge) @ $I_F = 2.0\text{A}$	VFM	1.1							V
Peak Reverse Current @ $T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_A = 100^\circ\text{C}$	IR	10 1.0							μA mA
Operating Temperature Range	Tj	-55 to +125							$^\circ\text{C}$
Storage Temperature Range	TSTG	-55 to +150							$^\circ\text{C}$

RATING AND CHARACTERISTIC CURVES (GBP2005-MS THRU GBP210-MS)

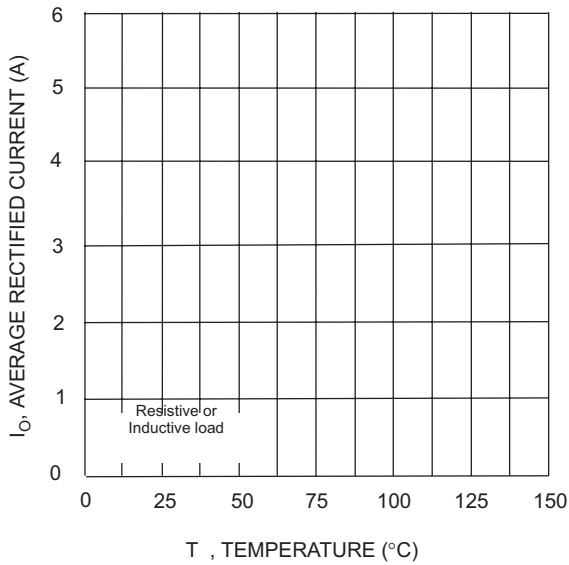


Fig. 1 Forward Current Derating Curve

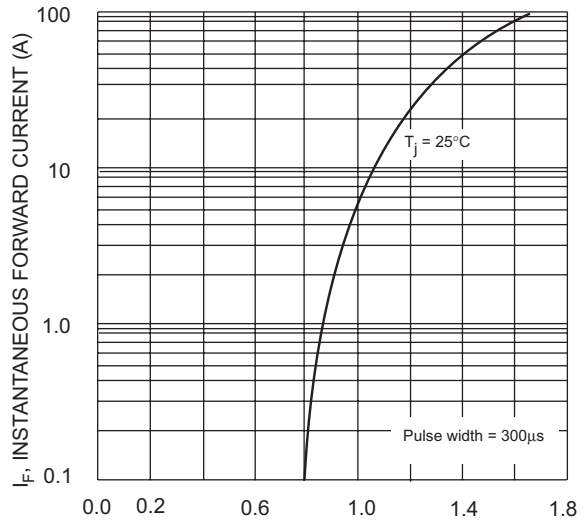


Fig. 2 Typical Fwd Characteristics, per element

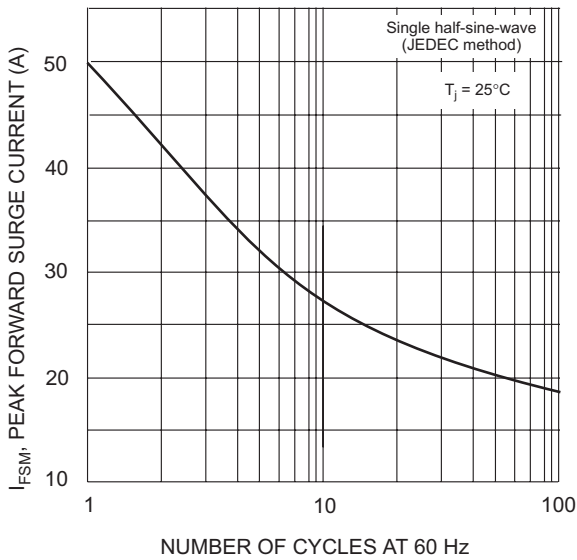


Fig. 3 Maximum Non-Repetitive Surge Current

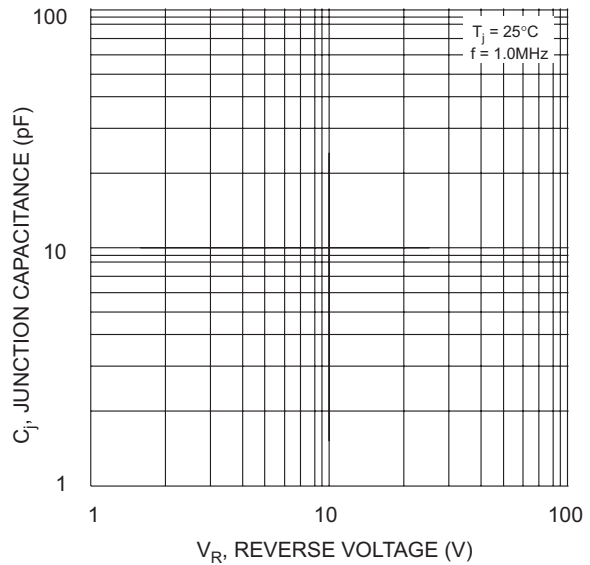
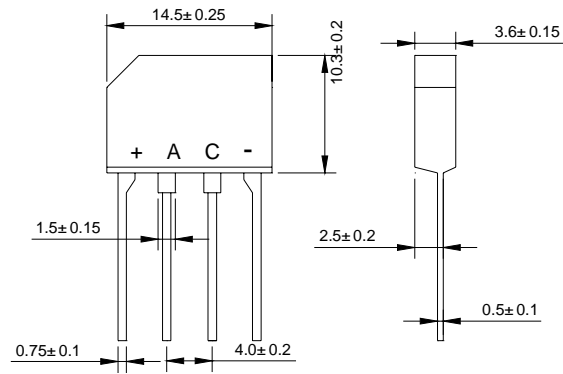


Fig. 4 Typical Junction Capacitance

PACKAGE MECHANICAL DATA

GBP



Dimensions in millimeters

REELS SPECIFICATION

P/N	PKG	QTY
GBP2005-MS THRU GBP210-MS	GBP	500

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